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Magnetocapacitance without magnetism

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A substantial magnetodielectric effect is often an indication of coupled magnetic and elastic order, such as is found in the multiferroics. However, it has recently been shown that magnetism is not necessary to produce either a magnetoresistance or a magnetocapacitance when the material is inhomogeneous [M. M. Parish and P. B. Littlewood, Phys. Rev. Lett. **101**, 166602 (2008)]. Here, we will investigate the characteristic magnetic-field-dependent dielectric response of such an inhomogeneous system using exact calculations and numerical simulations of conductor-dielectric composites. In particular, we will show that even simple conductor-dielectric layers exhibit a magnetocapacitance, and thus random bulk inhomogeneities are not a requirement for this effect. Indeed, this work essentially provides a natural generalisation of the Maxwell-Wagner effect to finite magnetic field. We will also discuss how this phenomenon has already been observed experimentally in some materials.

I. INTRODUCTION

Macroscopic inhomogeneities can have a surprising impact on the magnetotransport of a material. A spectacular example of this is the anomalous transverse magnetoresistance observed in doped silver chalcogenides [1, 2]. Here, the presence of inhomogeneities distorts the current paths in such a way that the Hall part is mixed into the longitudinal part of the response, thus giving rise to a large, linear magnetoresistance that persists across a range of magnetic fields and temperatures [3, 4]. Since this is a classical effect that does not require magnetism, it is relatively insensitive to temperature and thus potentially useful for technological applications. Indeed, inhomogeneities have already been exploited in the design of magnetic sensors: semiconductor devices with "extraordinary magnetoresistance" rely on the presence of a metallic inclusion to distort current and increase the device's resistance in a magnetic field [5, 6].

There are similar non-trivial effects in the case of the ac dielectric response: Catalan has shown that a material can display a substantial magnetocapacitance when an intrinsic magnetoresistance is combined with Maxwell-Wagner extrinsic effects such as contact effects and bulk inhomogeneities [7]. Subsequently, Littlewood and I showed that a magnetocapacitance can be induced by inhomogeneities alone and magnetism is not even necessary [8]. In particular, we found that a finite magnetic field induced a characteristic dielectric *resonance*, though no inductive element was present in the system. As we discuss below, this is a counter-intuitive phenomenon that every experimentalist should be aware of when probing the dielectric response of a material, particularly given that the existence of a magnetocapacitance is often taken as an indication of coupled ferroelectric and magnetic order. It is already known that composites consisting of a ferroelectric and a ferromagnet can generate a magnetoelectric coupling in the absence of any intrinsic coupling [9]. Here, we examine how simple conductor-dielectric composites can yield a dielectric response that depends on magnetic field in the absence of any magnetic or ferroelectric order. This effect is insensitive to the microscopics and is thus generic, being only dependent on the distribution of local capacitive and conductive regions. The only relevant material parameters are the static dielectric constant ε of the capacitive regions, and the resistivity tensor $\hat{\rho}$ (or conductivity tensor $\hat{\sigma} \equiv \hat{\rho}^{-1}$) in the conducting regions. As such, this magnetodielectric effect can occur in a variety of inhomogeneous materials: for instance, it has already been observed experimentally in nanoporous silicon [10, 11] and potentially in the manganite $La_{2/3}Ca_{1/3}MnO_3$ [12], as discussed in Sec. V.

In the following, we will investigate the characteristic magnetic-field-dependent dielectric response of two-dimensional (2D) conductor-dielectric composites using exact calculations, numerical simulations, and the effective medium approximation. In particular, we will show that even simple conductor-dielectric layers exhibit a magnetocapacitance, and thus random inhomogeneities in the bulk are not a requirement for this effect. Rather, it is sufficient to have conductor-dielectric interfaces that are perpendicular to the flow of current (or the movement of charges). This also appears to be consistent with experiment, since there is an observed link between magnetocapacitance and interfaces with free charges [13]. We will also discuss how an intrinsic magnetoresistance could enhance this effect.

II. MODEL AND METHODS

We consider a classical 2D composite medium consisting of purely dielectric regions (defined by dielectric constant ε) and purely conducting regions. The latter regions have the following resistivity tensor in a transverse magnetic field $\mathbf{H} = H\hat{z}$:

$$\hat{\rho} = \begin{pmatrix} \rho_{xx} & \rho_{xy} \\ -\rho_{xy} & \rho_{xx} \end{pmatrix} \tag{1}$$

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where we have assumed that the conductor is isotropic. We focus on the simplest case where $\rho_{xx} = \rho$ and $\rho_{xy}/\rho = \mu H \equiv \beta$, with μ the carrier mobility. Locally, the current $\mathbf{j}(\omega, \mathbf{r})$ is related to the electric field $\mathbf{E}(\omega, \mathbf{r})$ via Ohm's law $\mathbf{E}(\omega, \mathbf{r}) = \hat{\rho}(\omega, \mathbf{r})\mathbf{j}(\omega, \mathbf{r}) \equiv (i\omega\hat{\varepsilon}(\omega, \mathbf{r}))^{-1}\mathbf{j}(\omega, \mathbf{r})$, and globally the system is driven by electric field $\langle \mathbf{E}(\omega) \rangle$ at frequency ω, where $\langle ... \rangle$ corresponds to a volume average. The measured response averaged over the whole system is then the effective resistivity defined from $\langle \mathbf{E}(\omega) \rangle = \hat{\rho}_e(\omega)\langle \mathbf{j}(\omega) \rangle$. For the standard experimental setup where the boundary conditions are such that $\langle j_y \rangle = 0$ as in Fig. 1(a), the components of the dielectric function that are actually probed are then given by $\varepsilon_{xx}(\omega) = (i\omega\rho_{e,xx}(\omega))^{-1}$ and $\varepsilon_{xy}(\omega) = (i\omega\rho_{e,xy}(\omega))^{-1}$. The longitudinal response $\varepsilon_{xx}(\omega)$ is the usual dielectric response measured in experiment, while the transverse response $\varepsilon_{xy}(\omega)$ can be extracted from a measurement of the transverse electric field $E_y(\omega) = E_x(\omega)\varepsilon_{xx}(\omega)/\varepsilon_{xy}(\omega)$.

For the isotropic two-component media considered in Sec. IV, one can make use of the self-consistent effective medium approximation outlined in Refs. [14–16]. Here, we first imagine that we have a single inclusion embedded in an effective medium and then we average over all inclusions to self-consistently determine the response of this effective medium. This amounts to solving the coupled equations:

$$\sum_i p_i(\hat{\sigma}_i - \hat{\sigma}_e)\left(1 + \frac{\hat{\sigma}_i - \hat{\sigma}_e}{2\sigma_{e,xx}}\right) = 0 \tag{2}$$

where $\hat{\sigma}_e = \hat{\rho}_e^{-1}$ and p_i is the volume fraction of the i-th component. For the special case where the fractions are equal ($p_1 = p_2 = 1/2$), we can exploit a symmetry transformation for the electric field and current density [17–19] to derive an *exact* result for the effective dielectric function of the composite medium [8]. Note that the effective medium approximation recovers this exact result for equal fractions, and becomes formally exact in the limits $p_1 \to 0$, $p_2 \to 0$. Thus, we expect it to provide an accurate approach for investigating isotropic media across all volume fractions.

For composites with anisotropic inhomogeneities like the conductor-dielectric layers in Sec. III, one requires a more brute force numerical approach. In this case, we discretise the system into four-terminal elements as shown in Fig. 1(b), where the voltages V_i at the terminals of each element are linearly related to the currents I_i via an impedance matrix: $V_i = Z_{ij}I_j$. Note that each voltage is defined with respect to the element centre and incoming currents are defined as positive. In a purely conducting region, $Z_{ij} = \frac{\rho}{2}(\delta_{ij} + \beta M_{ij})$, where

$$M_{ij} = \frac{1}{2}\begin{pmatrix} 0 & -1 & 0 & 1 \\ 1 & 0 & -1 & 0 \\ 0 & 1 & 0 & -1 \\ -1 & 0 & 1 & 0 \end{pmatrix}. \tag{3}$$

In a purely dielectric region, we simply have $Z_{ij} = (2i\omega\varepsilon)^{-1}\delta_{ij}$. To simulate a given layed composite such as in Fig. 2, we construct an $N \times M$ rectangular network of these four-terminal elements and then take the limit of large N and M (keeping N/M and the proportions of each phase fixed). In general, the response converges rapidly to that of an infinite network.

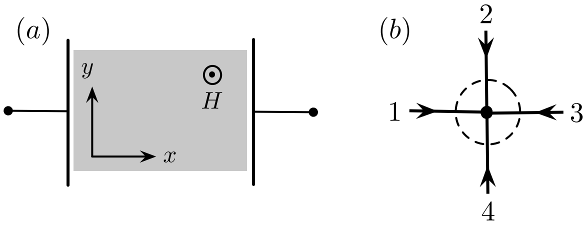

FIG. 1: The basics of probing and modelling dielectric response. Diagram (a) depicts the general measuring setup, where a rectangular sample is subjected to an oscillating electric field $E_x\hat{x}$ and a static transverse magnetic field H. The response of a general 2D conductor-dielectric composite can be simulated with a network of four-terminal elements (b).

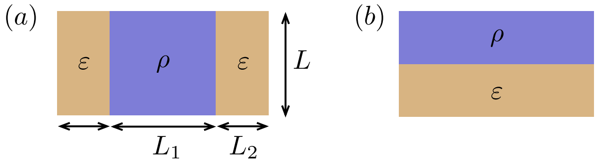

FIG. 2: Different configurations of conductor-dielectric layered composites, where $\langle j_y \rangle = 0$ on the upper and lower boundaries, and we have periodic boundary conditions for the left and right boundaries. The interfaces between conductor ρ and dielectric ε can be perpendicular (a) or parallel (b) to the current flow.

III. CONDUCTOR-DIELECTRIC INTERFACES

In this section, we consider simple conductor-dielectric layers (Fig. 2), which constitute the simplest realisation of anisotropic inhomogeneities. They also allow us to investigate the behaviour of conductor-dielectric interfaces and they can thus potentially describe the effect of contacts in experiment. Indeed, a magnetocapacitance has already been observed in non-magnetic Schottky barriers [20].

In general, we find that the behaviour is strongly dependent on geometry. When the conductor-dielectric interfaces are parallel to the current flow as in Fig. 2(b), the dielectric response does not depend on magnetic field and we simply obtain $\varepsilon_{xx}(\omega) = \varepsilon + (i\omega\rho)^{-1}$. By contrast, when the interfaces are perpendicular to the flow of charge as in Fig. 2(a), we have a substantial magnetodielectric effect. Firstly, at zero magnetic field, we recover the dielectric relaxation [21] expected from the Maxwell-Wagner effect — for a square unit with equal proportions of each phase, i.e. $L_1 = 2L_2 = L/2$ in Fig. 2(a), this gives

$$\varepsilon_{xx}(\omega) = 2\varepsilon \frac{1 - i\omega\tau}{1 + (\omega\tau)^2} \tag{4}$$

where the time constant $\tau = \rho\varepsilon$. Here, at the characteristic frequency $\omega\tau = 1$, there is a rapid change in $\Re[\varepsilon_{xx}]$ and an associated peak in $\Im[\varepsilon_{xx}]$. Then, in the presence of a magnetic field, the peak shifts to smaller $\omega\tau$ with increasing β as shown in Fig. 3. Indeed, at large fields $\beta \gg 1$, the characteristic frequency becomes $\beta\omega\tau = 1$ and the behaviour evolves into a dielectric resonance, where the capacitance $\Re[\varepsilon_{xx}]$ can become negative. This is similar to the magnetocapacitance of isotropic composite media [8] considered in Sec. IV. We also obtain a similar magnetodielectric effect for other configurations of Fig. 2(a), but the shift of the peak position in $\Im[\varepsilon_{xx}]$ often only approximately obeys $\beta\omega\tau = 1$.

To gain insight into this effect, we consider a modified version of the setup in Fig. 2(a) where we insert a perfectly conducting metallic interface between the conductor and dielectric. Now, if we ignore the dielectric for the moment and consider dc transport through the conductor, then such boundary conditions will give rise to a magnetoresistance [22]. In particular, if the conductor is square ($L_1 = L$), then the effective resistivity is exactly $\rho^*(H) = \rho\sqrt{1+\beta^2}$ [4, 23]. Thus, the response of the conductor-dielectric composite becomes (assuming $L_2 = L/2$):

$$\varepsilon_{xx}(\omega) = \frac{\varepsilon(1 - i\omega\tau\sqrt{1+\beta^2})}{1 + \omega^2\tau^2(1+\beta^2)} \tag{5}$$

In the limit $\beta \gg 1$, we essentially obtain Maxwell-Wagner relaxation with $\omega\tau$ replaced by $\beta\omega\tau$. Thus, we see that the effect of the interface is to mix the Hall component into the response (both real and imaginary parts) and replace ρ with the Hall resistivity $\rho\beta$. Note that we do not obtain a dielectric resonance here and thus it appears that this feature requires non-zero Hall fields E_y within the dielectric itself, which is not the case for perfectly conducting interfaces.

IV. ISOTROPIC COMPOSITE MEDIA

We now turn to the dielectric response of a 2D isotropic two-component medium where we once again have purely capacitive and purely resistive regions. When there are equal proportions of each component, we have the following exact results for the dielectric function [8]

$$\varepsilon_{xx}(\omega) = \varepsilon \frac{(1 + i\omega\tau)}{\sqrt{i\omega\tau}\sqrt{(1+i\omega\tau)^2 - (\omega\tau\beta)^2}} \tag{6}$$

$$\varepsilon_{xy}(\omega) = \frac{\varepsilon}{\beta}\left(1 - \frac{i}{\omega\tau}\right) \tag{7}$$

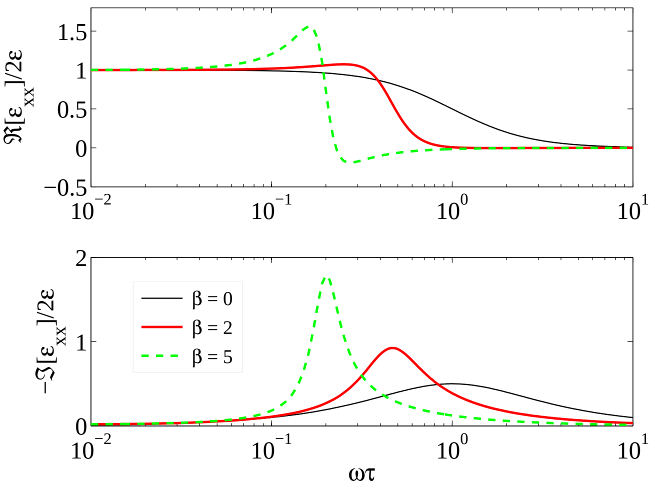

FIG. 3: Magnetodielectric effect in conductor-dielectric layers for the geometry in Fig. 2(a) with $L_1 = 2L_2 = L/2$. For $\beta = 0$ we have ordinary Maxwell-Wagner dielectric relaxation, while for $\beta > 1$ it becomes a dielectric resonance with characteristic frequency $\beta\omega\tau = 1$.

Note that $\varepsilon_{xx} \sim 1/\sqrt{\omega}$ in both low and high frequency limits, in contrast to the layered case with equal proportions. However, for $\beta > 1$, we have a dielectric resonance phenomenon similar to Fig. 3, with characteristic frequency $\beta\omega\tau = 1$.

We can also allow for the possibility that the resistive component has an intrinsic magnetoresistance $\rho_{xx}(H)$ by considering the more general expression for the resistivity tensor in Eq. (1). In this case, we obtain

$$\varepsilon_{xx}(\omega) = \varepsilon \frac{1 + i\omega\varepsilon\rho_{xx}}{\sqrt{i\omega\varepsilon\rho_{xx}}\sqrt{(1+i\omega\varepsilon\rho_{xx})^2 - \omega^2\varepsilon^2\rho_{xy}^2}} \tag{8}$$

Here, we find that the size of the magnetocapacitance (i.e. the change of $\Re[\varepsilon_{xx}(\omega)]/\varepsilon$ with β) depends crucially on the ratio ρ_{xy}/ρ_{xx}. Thus, we can have an enhanced magnetocapacitance for a *negative* intrinsic magnetoresistance, where $\rho_{xy}/\rho_{xx} \sim \rho\beta/\rho_{xx}$ is large at finite magnetic field. However, without a Hall component (i.e. $\rho_{xy} = 0$), we simply have $\varepsilon_{xx}(\omega) = \varepsilon/\sqrt{i\omega\epsilon\rho_{xx}}$ and we only have a magnetocapacitance when there is an intrinsic magnetoresistance $\rho_{xx}(H)$. In this case, we have no relaxation or resonance phenomena.

A. Effective medium approximation

To investigate all volume fractions of the components, we use the self-consistent effective medium approximation. Following Ref. [16], we simplify the problem by first transforming to a frame where the resistivity tensors of each phase are scalar. Thus we take

$$\mathbf{E}' = \mathbf{E} + b\hat{R}\rho\mathbf{J} \tag{9}$$

$$\mathbf{J}' = c\mathbf{J} + \hat{R}\rho^{-1}\mathbf{E} \tag{10}$$

where $\hat{R}$ is a rotation by 90 degrees:

$$\hat{R} = \begin{pmatrix} 0 & -1 \\ 1 & 0 \end{pmatrix} , \tag{11}$$

and the transformation constants are

$$\begin{aligned} b = & \frac{1}{2\rho_{xy}\rho} \left[\rho_{xx}^2 + \rho_{xy}^2 + \frac{\rho^2}{(\omega\tau)^2} \right. \\ & \left. + \sqrt{\left(\rho_{xx}^2 + \rho_{xy}^2 + \frac{\rho^2}{(\omega\tau)^2} \right)^2 - 4\frac{\rho_{xy}^2\rho^2}{(\omega\tau)^2}} \right] \\ c = & -\frac{1}{2\rho_{xy}\rho} \left[\rho_{xx}^2 + \rho_{xy}^2 + \frac{\rho^2}{(\omega\tau)^2} \right. \\ & \left. - \sqrt{\left(\rho_{xx}^2 + \rho_{xy}^2 + \frac{\rho^2}{(\omega\tau)^2} \right)^2 - 4\frac{\rho_{xy}^2\rho^2}{(\omega\tau)^2}} \right] , \end{aligned}$$

using Eq. (1) for the first component $\hat{\rho}_1$. Note that these coefficients are real, even though the dielectric phase (component 2) has a purely imaginary resistivity, $\rho_2 = (i\omega\varepsilon)^{-1}$. In the transformed frame, the (dimensionless) resistivities of the two components are

$$\frac{\rho_1'}{\rho} = \frac{\rho_{xx}}{\rho_{xy} + \rho c} , \qquad \frac{\rho_2'}{\rho} = -\frac{i}{\omega\tau c}$$

From Eq. (2), the effective resistivity of the transformed composite is then

$$\begin{aligned} \rho_e' = & \left(\frac{1}{2} - p \right) (\rho_1' - \rho_2') \\ & + \sqrt{\left(\frac{1}{2} - p \right)^2 (\rho_1' - \rho_2')^2 + \rho_1'\rho_2'} \end{aligned} \tag{12}$$

where p is the volume fraction of the dielectric phase. Transforming back to the original frame then yields the final result for the longitudinal effective resistivity:

$$\frac{\rho_{e,xx}}{\rho} = \frac{\rho\rho_e'}{\rho^2 + (\rho_e')^2}(b + c) \tag{13}$$

Note that taking equal proportions ($p = 1/2$) yields the exact result described earlier — we can recover Eq. (8) using $\epsilon_{xx}(\omega) = (i\omega\rho_{e,xx})^{-1}$. In what follows, we assume that we simply have $\rho_{xx} = \rho$ and $\rho_{xy} = \beta\rho$.

For all volume fractions p, one can show that there is always a dielectric resonance at $\beta\omega\tau = 1$ for large magnetic fields [8]. Moreover, we find that the dissipation at the peak only depends on p to leading order in β:

$$\frac{\rho_{e,xx}}{\rho} \simeq \frac{2}{1 - 2p + \sqrt{1 + 4p(1-p)}} + iO(1/\beta) \tag{14}$$

where we see that $\rho_{e,xx}/\rho \to \infty$ when $p \to 1$, as expected. Contrast this with the layered case (e.g. Eq. (5)), where we find that $\rho_{e,xx}/\rho$ at the peak increases with increasing magnetic field β.

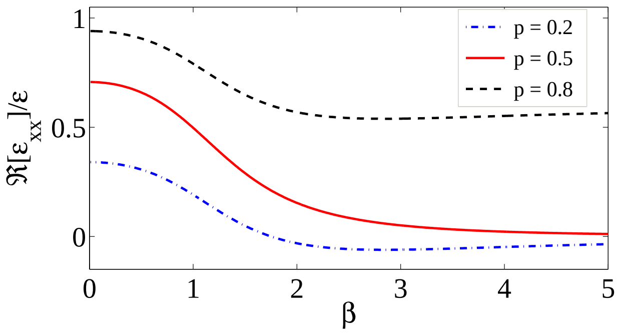

FIG. 4: Magnetocapacitance of isotropic conductor-dielectric composites at fixed frequency $\omega\tau = 1$ for different dielectric volume fractions p. In the limit of high magnetic field $\beta \to \infty$, $\Re[\varepsilon_{xx}]/\varepsilon \to 0$ and $\Re[\varepsilon_{xx}]/\varepsilon \to 2p-1$ for $p \le 1/2$ and $p > 1/2$, respectively.

If we fix the frequency ω, we also find a sizeable magnetocapacitance that depends on p. Figure 4 depicts the magnetocapacitance for $\omega\tau = 1$, and we see that both the size and sign of $\Re[\varepsilon_{xx}]/\varepsilon$ at large β is determined by p. Indeed, in the limit $\beta \to \infty$, $\Re[\varepsilon_{xx}]/\varepsilon$ only remains finite when $p > 1/2$ and the dielectric phase percolates through the whole sample.

Further insight can be obtained by deriving the limiting behaviour of the ac response from Eq. (13). Lets first consider the case where the magnetic field $\beta = 0$. Then in the limit $\omega\tau \to 0$, we have

$$\frac{\rho_{e,xx}}{\rho} \simeq \begin{cases} \frac{1}{1-2p} , & p < 1/2 \\ \frac{i}{\omega\tau}(1 - 2p) , & p > 1/2 \end{cases} \tag{15}$$

Likewise, in the limit $\omega\tau \to \infty$, we have

$$\frac{\rho_{e,xx}}{\rho} \simeq \begin{cases} 1 - 2p , & p < 1/2 \\ \frac{i}{\omega\tau}\frac{1}{1-2p} , & p > 1/2 \end{cases} \tag{16}$$

Here, we can clearly see the effect of percolation, since the conducting regions dominate the transport below the percolation threshold of the dielectric ($p < 1/2$), while the dielectric regions dominate above ($p > 1/2$). In particular, we see that the dependence on p is inverted for low and high frequencies, since the dielectric regions effectively behave insulating in the former case and metallic in the latter (where there is insufficient time for the dielectric to build up charge). However, for the special case $p = 1/2$, i.e. at the percolation threshold, we simply have $\rho_{e,xx} = \rho/\sqrt{i\omega\tau}$ and thus the same behaviour in both limits.

When there is a large magnetic field ($\beta \gg 1$), we obtain the same result for $\omega\tau \to 0$, or $\beta\omega\tau \ll 1$, but there can be markedly different behaviour when $\beta\omega\tau \gtrsim 1$. Specifically,

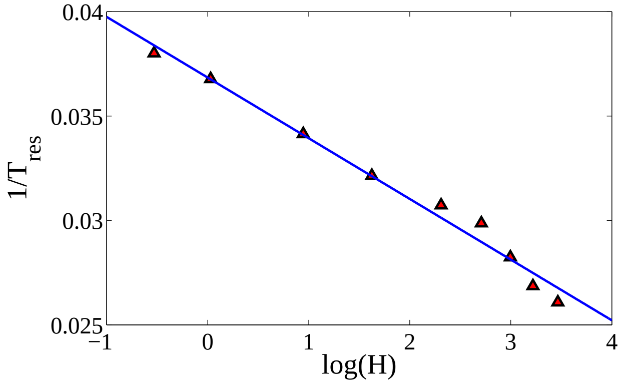

FIG. 5: Position of the resonance peak in the imaginary part of the dielectric response in terms of inverse temperature $1/T$ as a function of magnetic field H. Triangles are data for nanoporous silicon taken from Ref. [11], while the line corresponds to a fit from our classical model of conductor-dielectric composites.

for $\beta \to \infty$ and finite $\omega\tau$, we obtain

$$\frac{\rho_{e,xx}}{\rho} \simeq \begin{cases} \frac{1}{1-2p}\,, & p < 1/2 \\ \frac{\beta\sqrt{i\omega\tau}}{1+i\omega\tau}\,, & p = 1/2 \\ \frac{i}{\omega\tau}\frac{1}{1-2p}\,, & p > 1/2 \end{cases} \tag{17}$$

which matches the large β behaviour in Fig. 4. Note that for $p < 1/2$, the system at high frequencies behaves like one at low frequencies, Eq. (15). This implies that the dielectric region behaves insulating rather than metallic as one might normally expect at high frequencies. This is because at large magnetic field, the current paths are distorted such that they avoid any metallic region (cf. Ref. [5]) and thus any metal effectively behaves like an insulator.

V. DISCUSSION

The dielectric response investigated in this paper only depends on the presence of macroscopic inhomogeneities and can thus potentially be observed in a variety of materials. There is already evidence to suggest that it accounts for the magnetodielectric effect in graphene-polyvinyl alcohol nanocomposite films [24] and in nickel nanosheet-Na-4 mica composites [25]. Furthermore, our results are possibly relevant to rough interfaces in heterostructures [26].

Experiments on nanoporous silicon [10, 11] have revealed a magnetic-field-dependent dielectric resonance that is consistent with our model. In this case, the dielectric response was measured at fixed frequency $\omega = 100$ kHz as a function of temperature $T = 25$–40 K and magnetic field $H = 0$–32 T. However, varying the temperature is equivalent to varying $\omega\tau$ if we approximate ε as temperature independent and the electrical transport in the semiconductor as being activated: $\rho = \rho_0 e^{\Delta/k_B T}$, where Δ is the activation gap. Then our predicted resonance occurs at the temperature $k_B T = -\Delta/\log(\beta\omega\varepsilon\rho_0)$, so that the dielectric resonance shifts to higher T with increasing H, as indeed was observed in experiment. Assuming that $\beta = 1$ corresponds to $H \simeq$ 1T, we can fit the data with $\omega_0 \equiv 1/\rho_0\varepsilon \simeq 4 \times 10^{10}$ Hz and $\Delta \simeq 30$ meV, as shown in Fig. 5. Note that the size of Δ is consistent with activation from an impurity band.

Our effect may also be relevant to the dielectric resonance observed in the manganite $\mathrm{La}_{2/3}\mathrm{Ca}_{1/3}\mathrm{MnO}_3$ just above the ferromagnetic transition temperature [12]. However, here the situation is more complex since there is magnetism involved and the effective "composite" corresponds to the phase separation between magnetic metal and charge-ordered insulator. Moreover, the size of magnetic metallic domains could change with magnetic field. This all requires further investigation: in principle, one might be able to probe the latter possibility by measuring the Hall component ε_{xy}, as discussed in Ref. [8].

Finally, with regards to experiment, there is the question of when our classical model breaks down as the size of the sample is reduced. Formally, our approach is only valid when $1/\omega$ is greater than any microscopic timescale, e.g., the scattering time of charge carriers within the conducting regions, and when the size of the inhomogeneities is greater than any microscopic lengthscale, e.g., mean free path. However, one may be able to extend our results to smaller sizes using an appropriately redefined ε and $\hat{\rho}$.

VI. CONCLUSION

In this paper, we have investigated 2D conductor-dielectric composites and we have shown how these can produce a magnetic-field-dependent dielectric response without any magnetism. Using exact results and the effective medium approximation, we have derived expressions for the dielectric response of isotropic composite media and we have explicitly revealed the behaviour at the resonance $\beta\omega\tau = 1$ and in the limits $\omega\tau \to 0$, $\omega\tau \to \infty$ and $\beta \to \infty$. Moreover, we find that an intrinsic magnetoresistance could enhance this magnetodielectric effect from inhomogeneities. We have also performed numerical simulations of layered composites to show that conductor-dielectric interfaces play a key role in this phenomenon. Finally, we have discussed how our predicted magnetodielectric effect has already been observed experimentally in some materials. An open question is how our results generalise to higher dimensions and this will be the subject of future work.

Acknowledgments

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